End of Life January 2025 - Alternative Device: VGSOTxx

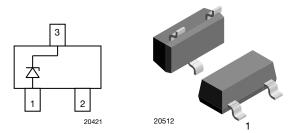


www.vishay.com

GSOT03 to GSOT36

Vishay Semiconductors

Single-Line ESD Protection in SOT-23



MARKING (example only)



YYY = type code (see table below) XX = date code

LINKS TO ADDITIONAL RESOURCES



SPICE Models

FEATURES

- Single-line ESD protection device
- ESD immunity acc. IEC 61000-4-2 ± 30 kV contact discharge ± 30 kV air discharge
- ESD capability according to AEC-Q101: human body model: class H3B: > 8 kV
- Space saving SOT-23 package
- e3 Sn
- AEC-Q101 qualified available
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

ORDERING INFORMATION									
	ENVIR	ONMENTAL AND QUALITY CODE			PACKAG				
PART NUMBER (EXAMPLE)	AEC-Q101 QUALIFIED	RoHS-CON LEAD (P		TIN PLATED	3K PER 7" REEL (8 mm TAPE),	10K PER 13" REEL (8 mm TAPE),	ORDERING CODE (EXAMPLE)		
		STANDARD	GREEN	REEN PLATED 15K/BOX = MOQ		10K/BOX = MOQ			
GSOT05-		E		3	-08		GSOT05-E3-08		
GSOT05-			G	3	-08		GSOT05-G3-08		
GSOT05-	Н	E		3	-08		GSOT05-HE3-08		
GSOT05-	Н		G	3	-08		GSOT05-HG3-08		
GSOT05-		E		3		-18	GSOT05-E3-18		
GSOT05-			G	3		-18	GSOT05-G3-18		
GSOT05-	Н	E		3		-18	GSOT05-HE3-18		
GSOT05-	Н		G	3		-18	GSOT05-HG3-18		

PACKA	PACKAGE DATA									
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS			
GSOT03	SOT-23	03	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature max. 260 °C			
000100	001 20	03G	Green	8.1 mg	020470	(according J-STD-020)				
GSOT04	SOT-23	04	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature max. 260 °C			
000104	001 20	04G	Green	8.1 mg	02 04 0 0	(according J-STD-020)	1 car temperature max. 200 0			
GSOT05	SOT-23	05	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature max. 260 °C			
030103	301-23	05G	Green	8.1 mg	(according J-STD-02		Teak temperature max. 200 0			
GSOT08	SOT-23	08	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature max. 260 °C			
030108	301-23	08G	Green	8.1 mg	0L 94 V-0	(according J-STD-020)	Feak temperature max. 200 C			
GSOT12	SOT-23	12	Standard	8.8 mg	UL 94 V-0	MSL level 1	Book tomporature max 260 °C			
G30112	301-23	12G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	Peak temperature max. 260 °C			
GSOT15	SOT-23	15	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature max. 260 °C			
630115	301-23	15G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	Feak temperature max. 200 C			
GSOT24	SOT 00	24	Standard	8.8 mg	UL 94 V-0	MSL level 1	Deals temperature may 260 °C			
GS0124	SOT-23	24G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	Peak temperature max. 260 °C			
CCOT26	SOT 00	36	Standard	8.8 mg		MSL level 1	Deals temperature may 260 °C			
GSOT36	SOT-23	36G	Green	8.1 mg	UL 94 V-0 (according J-STD-		Peak temperature max. 260 °C			

Rev. 2.9, 13-Feb-2025

1 For technical questions, contact: <u>ESDprotection@vishay.com</u> Document Number: 85807

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishav.com/doc?91000



RoHS

COMPLIANT

HALOGEN

FREE

GREEN (5-2008)



GSOT03 to GSOT36

Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS GSOT03							
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	I _{PPM}	30	А			
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	369	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV			
ESD initiduity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV			
Operating temperature	Junction temperature	TJ	-40 to +125	°C			
Storage temperature		T _{STG}	-55 to +150	°C			

ABSOLUTE MAXIMUM RATINGS GSOT04						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	30	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	429	W		
	Contact discharge acc. IEC 61000-4-2; 10 pulses	N/	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT05							
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	I _{PPM}	30	А			
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	480	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV			
ESD Immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV			
Operating temperature	Junction temperature	TJ	-40 to +125	°C			
Storage temperature		T _{STG}	-55 to +150	°C			

ABSOLUTE MAXIMUM RATINGS GSOT08						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	18	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	345	W		
	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

Rev. 2.9, 13-Feb-2025

2



GSOT03 to GSOT36

Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS GSOT12							
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	12	А			
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	312	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV			
ESD minumity	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV			
Operating temperature	Junction temperature	TJ	-40 to +125	°C			
Storage temperature		T _{STG}	-55 to +150	°C			

ABSOLUTE MAXIMUM RATINGS GSOT15						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	8	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	230	W		
	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT24						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	5	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	235	W		
	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT36						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	3.5	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	248	W		
	Contact discharge acc. IEC 61000-4-2; 10 pulses	N/	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

3

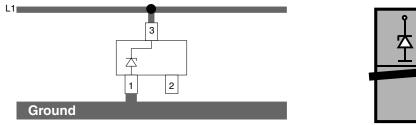


GSOT03 to GSOT36

Vishay Semiconductors

BIAs-MODE (1-line Bidirectional Asymmetrical protection mode)

With the GSOTxx one signal- or data-lines (L1) can be protected against voltage transients. With pin 1 connected to ground and pin 3 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified maximum reverse working voltage (V_{RWM}) the protection diode between pin 1 and pin 3 offers a high isolation to the ground line. The protection device behaves like an open switch. As soon as any positive transient voltage signal exceeds the breakdown voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The clamping voltage (V_C) is defined by the breakdown voltage (V_{BB}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection diode. Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction through the protection diode. The low forward voltage (VF) clamps the negative transient close to the ground level. Due to the different clamping levels in forward and reverse direction the GSOTxx clamping behavior is Bidirectional and Asymmetrical (BiAs).



²⁰⁴²²

BiAs

ELECTRICAL CHARACTERISTICS GSOT03 (T_{amb} = 25 °C unless otherwise specified) between pin 3 and pin 1							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines	
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	3.3	V	
Reverse voltage	at I _R = 100 μA	V _R	3.3	-	-	V	
Reverse current	at V _R = 3.3 V	I _R	-	-	100	μA	
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	4	4.6	5.5	V	
	at I _{PP} = 1 A	V	-	5.7	7.5	V	
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	10	12.3	V	
Forward elemening voltage	at I _{PP} = 1 A	V	-	1	1.2	V	
Forward clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V _F	-	4.5	-	V	
Canacitanas	at $V_R = 0 V$; f = 1 MHz	0	-	420	600	pF	
Capacitance	at V _R = 1.6 V; f = 1 MHz	C _D	-	260	-	pF	

ELECTRICAL CHARACTERISTICS GSOT04 ($T_{amb} = 25$ °C unless otherwise specified) between pin 3 and pin 1								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	4	V		
Reverse voltage	at I _R = 20 μA	V _R	4	-	-	V		
Reverse current	at V _R = 4 V	I _R	-	-	20	μA		
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	5	6.1	7	V		
Reverse clamping voltage	at I _{PP} = 1 A	V	-	7.5	9	V		
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V _C	-	11.2	14.3	V		
Forward elemping voltage	at I _{PP} = 1 A	V	-	1	1.2	V		
Forward clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V _F	-	4.5	-	V		
Canacitanaa	at V _R = 0 V; f = 1 MHz	<u> </u>	-	310	450	pF		
Capacitance	at V _R = 2 V; f = 1 MHz	C _D	-	200	-	pF		

Rev. 2.9, 13-Feb-2025

4



GSOT03 to GSOT36

Vishay Semiconductors

ELECTRICAL CHARAC between pin 3 and pin 1	TERISTICS GSOT05 (T _{amb} = 25 °C	C unless ot	herwise s	pecified)		
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	5	V
Reverse voltage	at I _R = 10 μA	V _R	5	-	-	V
Reverse current	at V _R = 5 V	I _R	-	-	10	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	6	6.8	8	V
	at I _{PP} = 1 A	V _C	-	7	8.7	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A		-	12	16	V
	at I _{PP} = 1 A	V _F	-	1	1.2	V
Forward clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$		-	4.5	-	V
Capacitance	at $V_R = 0 V$; f = 1 MHz	C _D	-	260	350	pF
	at V _R = 2.5 V; f = 1 MHz		-	150	-	pF

ELECTRICAL CHARACTERISTICS GSOT08 (T_{amb} = 25 °C unless otherwise specified) between pin 3 and pin 1

between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	8	V
Reverse voltage	at I _R = 5 µA	V _R	8	-	-	V
Reverse current	at V _R = 8 V	I _R	-	-	5	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	9	10	11	V
Reverse clamping voltage	at I _{PP} = 1 A	- V _C	-	10.7	13	V
	at I _{PP} = I _{PPM} = 18 A		-	15.2	19.2	V
Forward elemping valtage	at I _{PP} = 1 A	N	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 18 A	V _F	-	3	-	V
Orneriterer	at $V_R = 0 V$; f = 1 MHz	- C _D	-	160	250	pF
Capacitance	at V _R = 4 V; f = 1 MHz		-	80	-	pF

ELECTRICAL CHARACE between pin 3 and pin 1	TERISTICS GSOT12 (T _{amb} = 25 °C	C unless ot	herwise s	pecified)		
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	12	V
Reverse voltage	at I _R = 1 μA	V _R	12	-	-	V
Reverse current	at V _R = 12 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	13.5	15	16.5	V
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	15.4	18.7	V
	at I _{PP} = I _{PPM} = 12 A		-	21.2	26	V
Forward clamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V
	at I _{PP} = I _{PPM} = 12 A		-	2.2	-	V
Capacitance	at $V_R = 0 V$; f = 1 MHz	CD	-	115	150	pF
	at V _R = 6 V; f = 1 MHz		-	50	-	pF



GSOT03 to GSOT36

Vishay Semiconductors

ELECTRICAL CHARAC between pin 3 and pin 1	TERISTICS GSOT15 (T _{amb} = 25 °C	C unless ot	herwise s	pecified)		
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	15	V
Reverse voltage	at I _R = 1 μA	V _R	15	-	-	V
Reverse current	at V _R = 15 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	16.5	18	20	V
Deverse elemeine veltage	at I _{PP} = 1 A	- V _C	-	19.4	23.5	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 8 A		-	24.8	28.8	V
Forward clamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V
	at I _{PP} = I _{PPM} = 8 A		-	1.8	-	V
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	90	120	pF
	at V _R = 7.5 V; f = 1 MHz		-	35	-	pF

ELECTRICAL CHARACTERISTICS GSOT24 ($T_{amb} = 25$ °C unless otherwise specified) between pin 3 and pin 1

between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	24	V
Reverse voltage	at I _R = 1 μA	V _R	24	-	-	V
Reverse current	at V _R = 24 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	27	30	33	V
Reverse clamping voltage	at I _{PP} = 1 A	- V _C	-	34	41	V
	at $I_{PP} = I_{PPM} = 5 A$		-	41	47	V
Forward clamping voltage	at I _{PP} = 1 A	V	-	1	1.2	V
Forward clamping voltage	at $I_{PP} = I_{PPM} = 5 A$	V _F	-	1.4	-	V
Capacitance	at $V_R = 0 V$; f = 1 MHz	- C _D	-	65	80	pF
	at V _R = 12 V; f = 1 MHz		-	20	-	pF

ELECTRICAL CHARAC	TERISTICS GSOT36 (T _{amb} = 25 °C	C unless ot	herwise s	pecified)		
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	36	V
Reverse voltage	at I _R = 1 μA	V _R	36	-	-	V
Reverse current	at V _R = 36 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	39	43	47	V
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	49	60	V
	at I _{PP} = I _{PPM} = 3.5 A		-	59	71	V
Forward clamping voltage	at I _{PP} = 1 A	N	-	1	1.2	V
	at I _{PP} = I _{PPM} = 3.5 A	V _F	-	1.3	-	V
Capacitance	at $V_R = 0$ V; f = 1 MHz	0	-	52	65	pF
	at $V_{B} = 18$ V; f = 1 MHz	CD	-	12	-	۶

Rev. 2.9, 13-Feb-2025

6

End of Life January 2025 - Alternative Device: VGSOTxx

I_{ESD} (%)



www.vishay.com

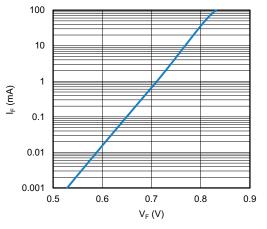


Fig. 1 - Typical Forward Current I_F vs. Forward Voltage V_F

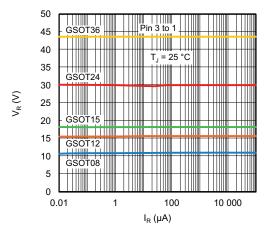


Fig. 2 - Typical Reverse Voltage V_R vs. Reverse Current I_R

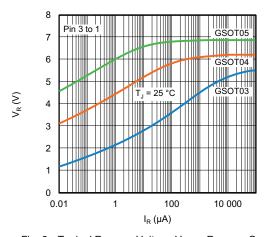


Fig. 3 - Typical Reverse Voltage V_{R} vs. Reverse Current I_{R}

120 100 80 60 53 40

GSOT03 to GSOT36

Vishay Semiconductors

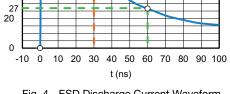


Fig. 4 - ESD Discharge Current Waveform According to IEC 61000-4-2 (330 $\Omega\,/$ 150 pF)

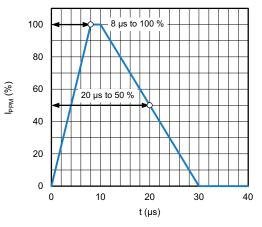


Fig. 5 - 8/20 µs Peak Pulse Current Waveform According to IEC 61000-4-5

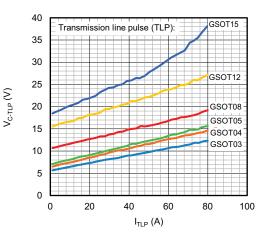


Fig. 6 - Typical Clamping Voltage vs. Peak Pulse Current

Rev. 2.9, 13-Feb-2025

For technical questions, contact: ESDprotection@vishay.com

Document Number: 85807

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishav.com/doc?91000

End of Life January 2025 - Alternative Device: VGSOTxx



GSOT03 to GSOT36

Vishay Semiconductors

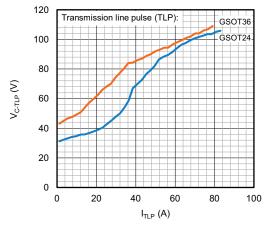


Fig. 7 - Typical Clamping Voltage vs. Peak Pulse Current

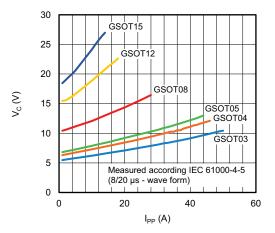


Fig. 8 - Typical Peak Clamping Voltage vs. Peak Pulse Current

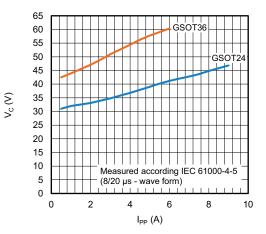


Fig. 9 - Typical Peak Clamping Voltage vs. Peak Pulse Current

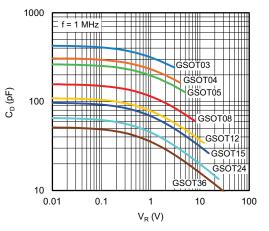


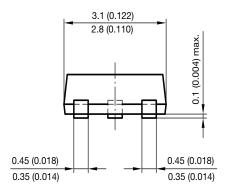
Fig. 10 - Typical Capacitance vs. Reverse Voltage

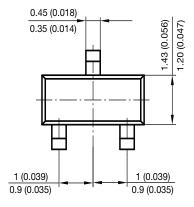


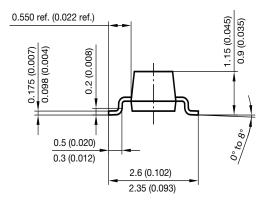
GSOT03 to GSOT36

Vishay Semiconductors

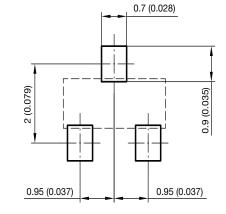
PACKAGE DIMENSIONS in millimeters (inches): SOT-23



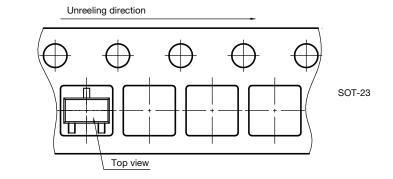




Foot print recommendation:



Document no.: 6.541-5014.01-4 Rev. 8 - Date: 23. Sep. 2009 17418



Orientation in carrier tape SOT-23 S8-V-3929.01-006 (4) 04.02.2010 22607



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2025 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

Revision: 01-Jan-2025

1